

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently Amended) A semiconductor device comprising:

a semiconductor substrate;

a first insulating film formed above the semiconductor substrate and having a relative dielectric constant of 3.8 or less;

a conductor which covers a side face of the first insulating film at least near four corners of the semiconductor substrate, and ~~at least an outer side face of which has~~ includes a conductive barrier layer on at least an outer side face thereof; and

a second insulating film covering the ~~outer side face~~ conductive barrier layer of the conductor and having a relative dielectric constant of over 3.8,

wherein the first insulating film and the second insulating film are positioned so as to directly sandwich the conductor at least a part of the second insulating film being formed at a same distance from first horizontal level above the semiconductor substrate as a part of the first insulating film and also at a second horizontal level higher than the first horizontal level above the semiconductor substrate.

2. (Currently Amended) A semiconductor device as set forth in claim 1, wherein the conductive barrier layer that the conductor ~~contains~~ includes one kind selected from a group consisting of titanium (Ti), tantalum (Ta), zirconium (Zr), and tungsten (W), and

the conductor contains as a major component one kind selected from a group consisting of copper (Cu), aluminum (Al), and tin (Sn).

3.-6. (Canceled)

7. (Previously Presented) A semiconductor device as set forth in claim 1,  
wherein the second insulating film is extended so as to cover an upper side of  
the first insulating film, the semiconductor device further comprising  
a conductor pattern passing through the second insulating film positioned on the  
upper side of the first insulating film.

8. (Canceled)

9. (Original) A semiconductor device as set forth in claim 7, further comprising a  
conductive pattern buried in the first insulating film.

10. (Canceled)

11. (Original) A semiconductor device as set forth in claim 1, wherein the first  
insulating film is constituted of a plurality of layers.

12. (Canceled)

13. (Original) A semiconductor device as set forth in claim 1, wherein the conductor is formed in a ring shape covering an entire side face of the first insulating film.

14. (Canceled)

15. (Original) A semiconductor device as set forth in claim 1, wherein the second insulating film is at least one kind selected from a group consisting of silicon oxide ( $\text{SiO}_2$ ), silicon nitride ( $\text{SiN}$ ), silicon carbide ( $\text{SiC}$ ), and silicon carbonitride ( $\text{SiCN}$ ).

16.-20. (Canceled)